

General Description

The WST05N10 is the highest performance trench N-Ch MOSFET with extreme high cell density , which provide excellent $R_{DS(ON)}$ and gate charge for most of the small power switching and load switch applications.

The WST05N10 meet the RoHS and Green Product requirement with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

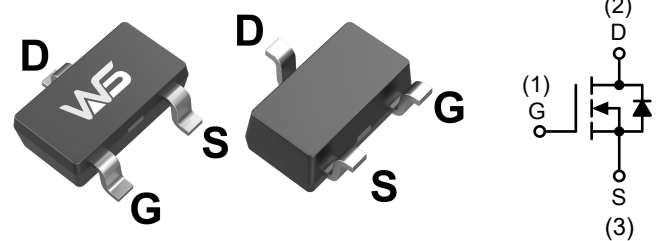
Product Summery

BV_{DSS}	$R_{DS(ON)}$	I_D
100V	135m Ω	2.8A

Applications

- High Frequency Point-of-Load Synchronous Small power switching for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

SOT-23-3L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_c=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	2.8	A
$I_D@T_c=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	1.2	A
I_{DM}	Pulsed Drain Current ²	7	A
$P_D@T_c=25^\circ\text{C}$	Total Power Dissipation ³	1	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	300	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	150	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
ΔBV _{DSS} /ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.067	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =1A	---	135	145	mΩ
		V _{GS} =4.5V, I _D =0.5A	---	150	220	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.5	2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	-4.2	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	5	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =1A	---	2.4	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.8	5.6	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =80V, V _{GS} =10V, I _D =1A	---	15	25	nC
Q _{gs}	Gate-Source Charge		---	3.2	5.2	
Q _{gd}	Gate-Drain Charge		---	4.7	7.8	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω I _D =1A	---	3.2	7.4	ns
T _r	Rise Time		---	11	16	
T _{d(off)}	Turn-Off Delay Time		---	9.1	25	
T _f	Fall Time		---	35	57	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	690	711	pF
C _{oss}	Output Capacitance		---	120	41	
C _{rss}	Reverse Transfer Capacitance		---	90	23	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	2.8	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	5	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	IF=1A, dI/dt=100A/μs, T _J =25°C	---	16	---	nS
Q _{rr}	Reverse Recovery Charge		---	10.2	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, t<10sec.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

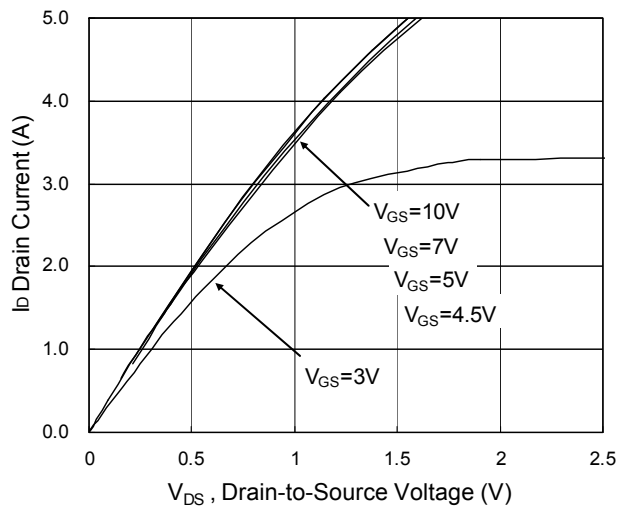


Fig.1 Typical Output Characteristics

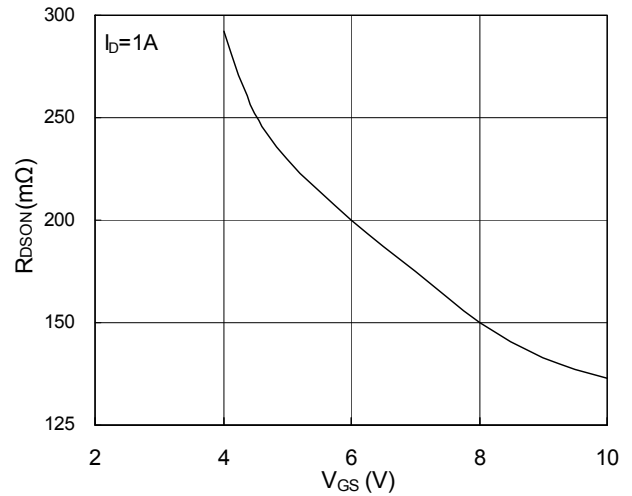


Fig.2 On-Resistance vs. Gate-Source

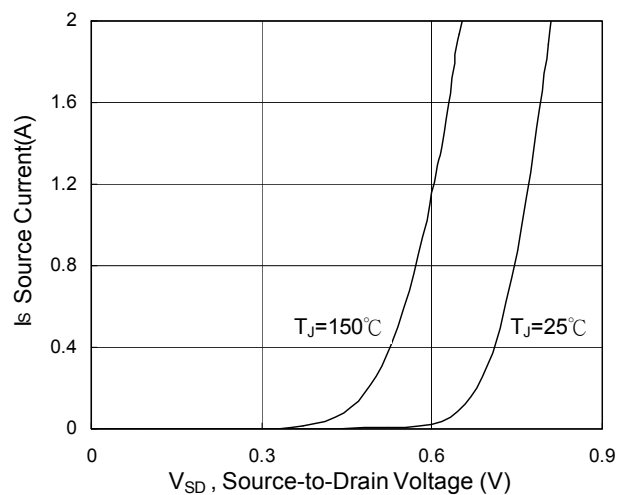


Fig.3 Forward Characteristics of Reverse

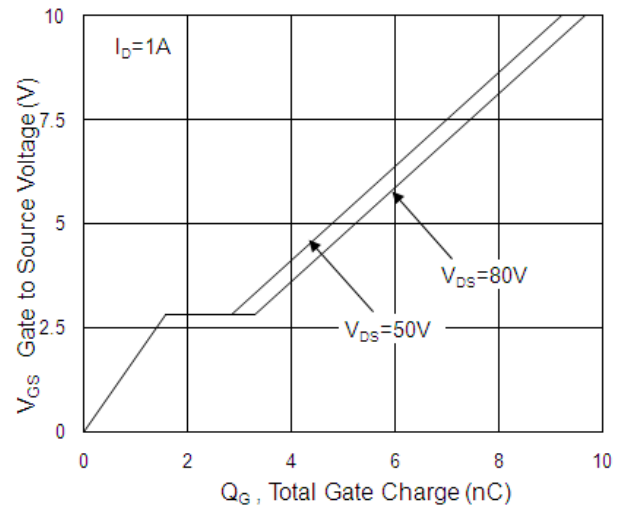


Fig.4 Gate-Charge Characteristics

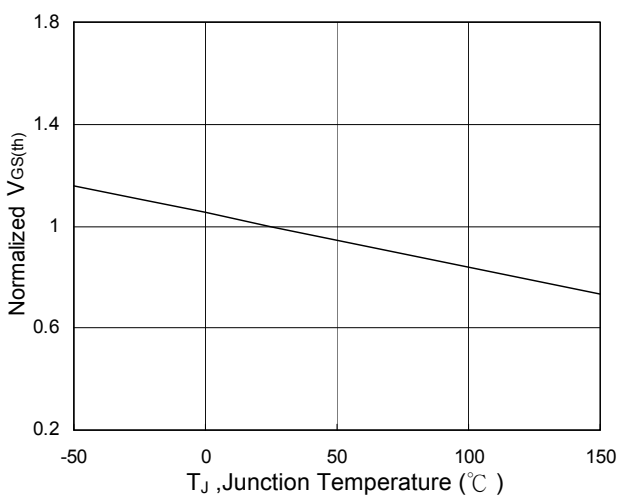


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

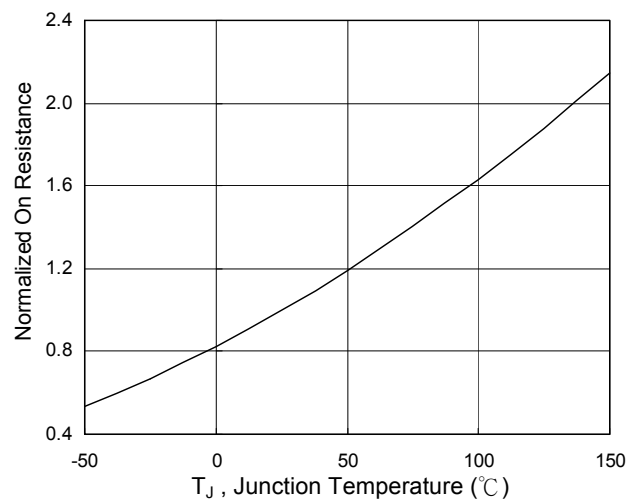
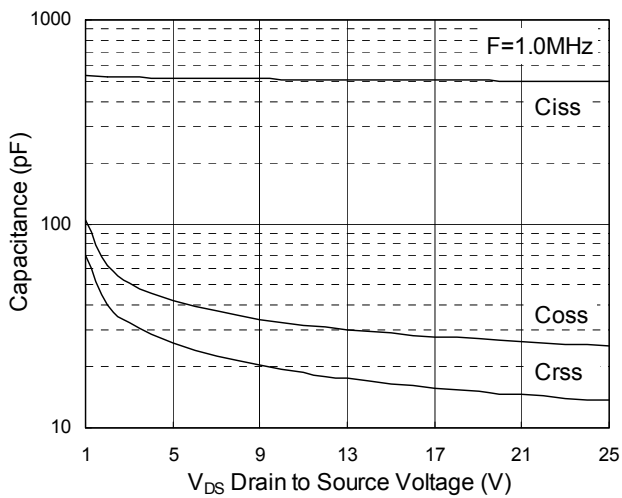
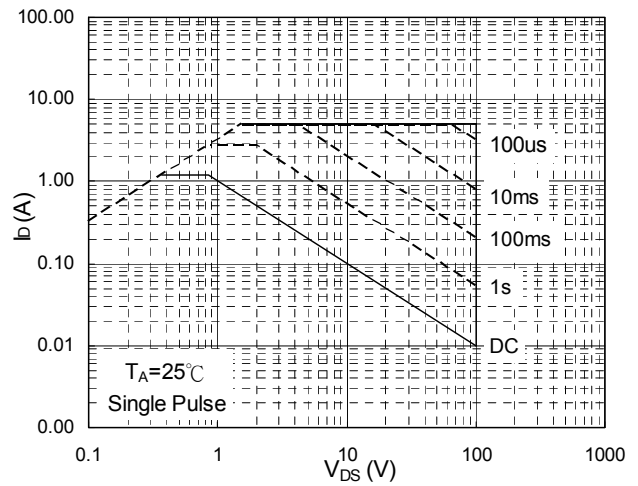
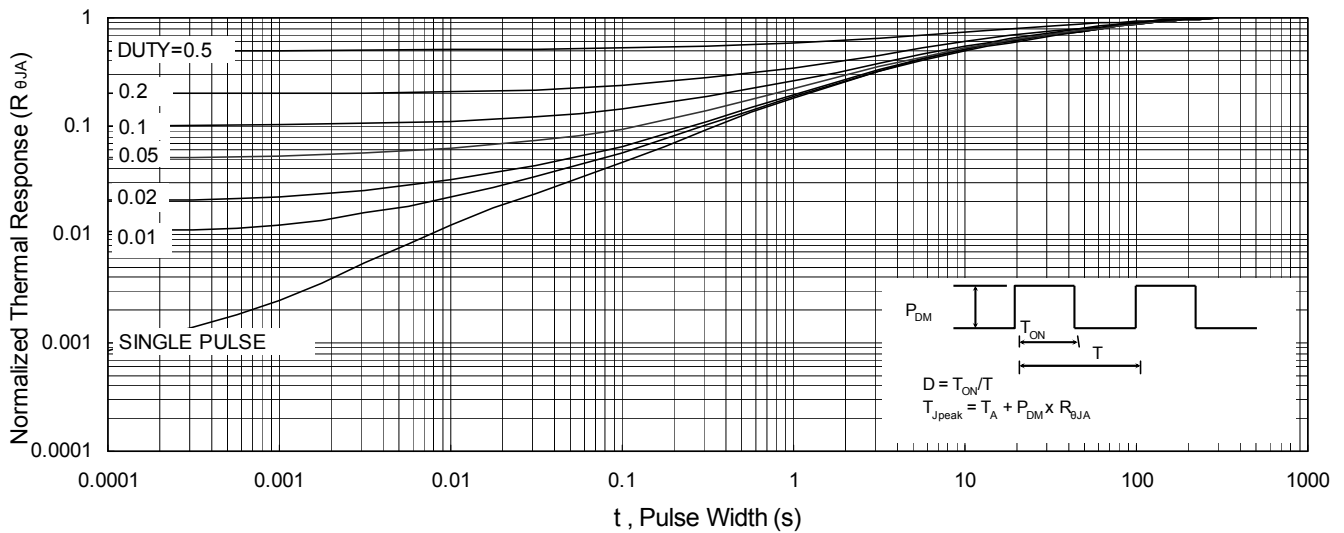
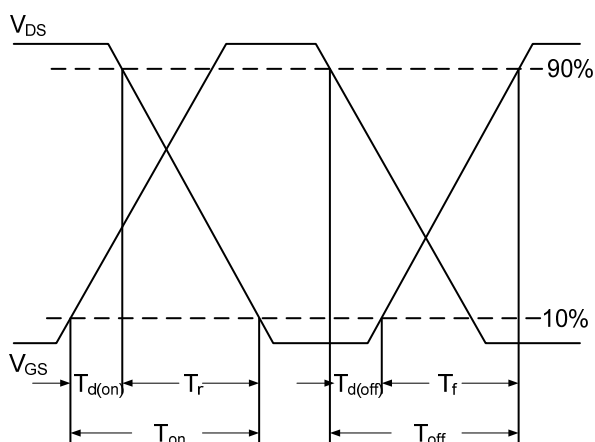
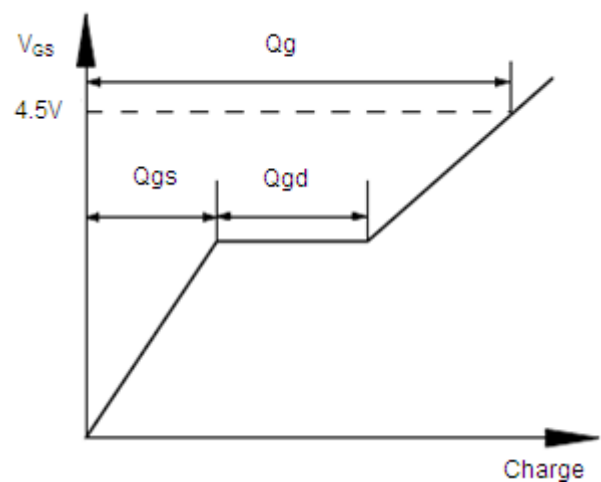
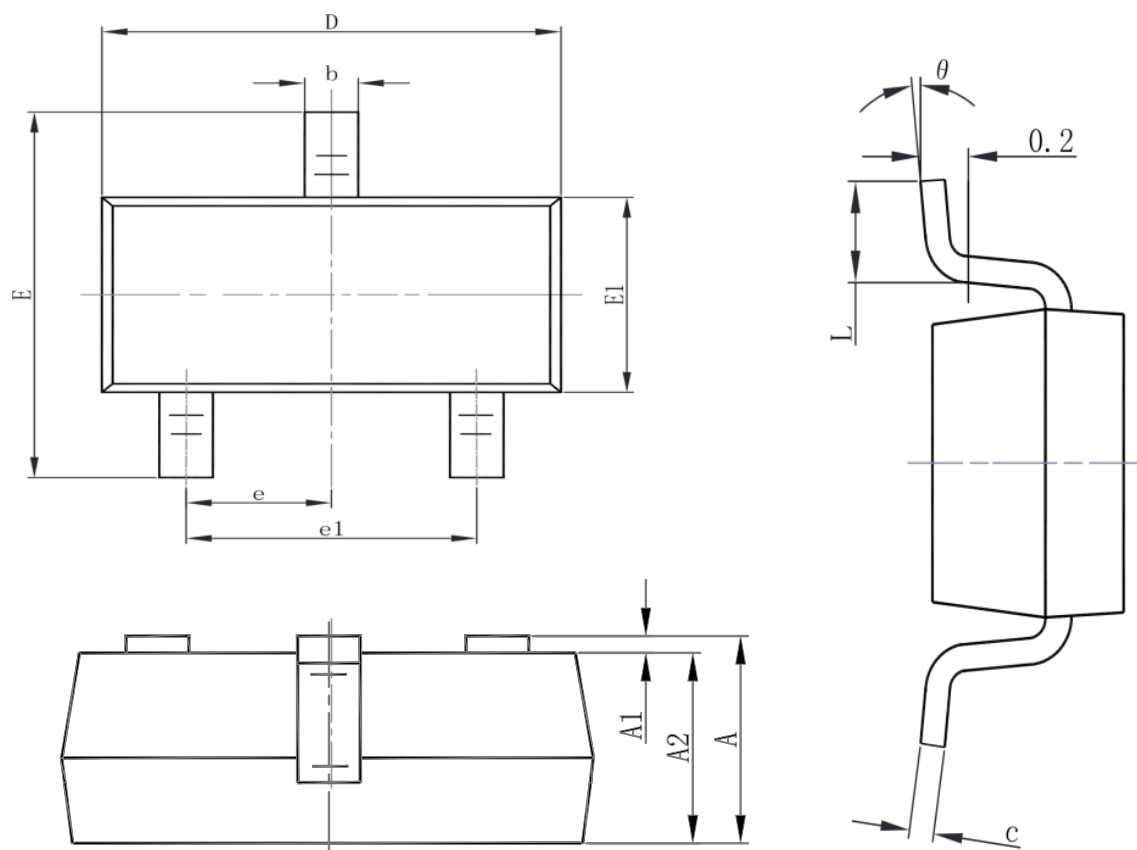


Fig.6 Normalized $R_{DS(on)}$ vs. T_J


Fig.7 Capacitance

Fig.8 Safe Operating Area

Fig.9 Normalized Maximum Transient Thermal Impedance

Fig.10 Switching Time Waveform

Fig.11 Gate Charge Waveform

Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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